



Single Wafer System to Enable High Volume Production of Highly-Efficient GaN Power Devices



Propel[®] emPower[™] GaN MOCVD System

Clusterable platform accelerates the adoption of GaN-based Power and RF devices by achieving the highest performance at the lowest cost of ownership

- > Unparalleled performance for thickness and composition uniformity, dopant control and defects
- > TurboDisc technology with exceptional long campaign production throughput
- > Best-in-class flexibility with wide process window and ease of operation
- > Lowest cost of ownership with industry's highest production uptime



Veeco's *emPower* Advantage

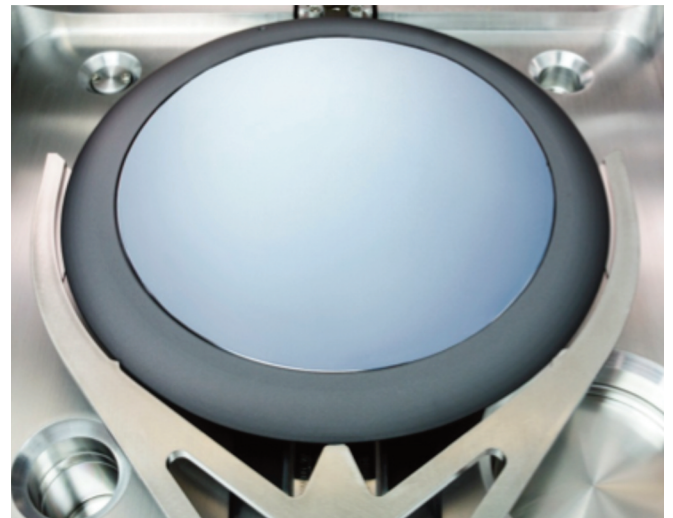
Propel *emPower* is Veeco's multi chamber MOCVD system designed specifically for the high-volume GaN power electronics and GaN RF industry. Featuring single-wafer reactor based platform capable of processing 150mm and 200mm wafers with high-quality GaN films deposits that result in highly efficient power electronic and industry leading RF devices.

Next Generation Performance with Productivity Advantage

- > Designed for Superior Thermal and Thickness Uniformity
- > Scalable to Large wafer size for next generation Technology
- > High volume Production ready with superior wafer to wafer and run to run stability
- > Ease of operation with minimum process tuning

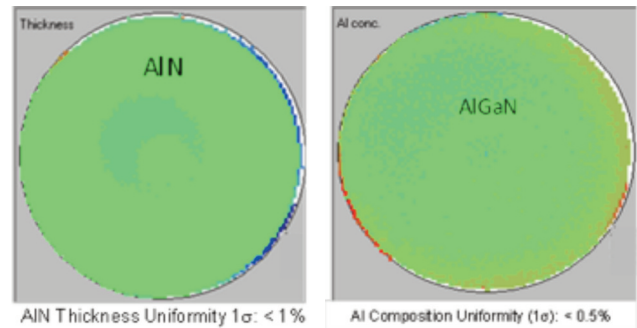
Configurations and Use Cases

Category	Description
Architecture	Single Wafer reactor based multi-chamber system
Available Configurations	2, 4 or 6 chamber configuration
Applications	GaN Power and GaN RF
Substrate Materials	Si & SiC
Wafer Sizes	4", 6" and 8"

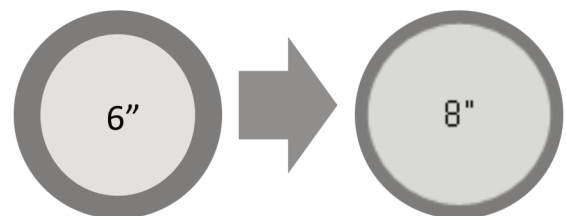


- > TurboDisc® Single Wafer Reactor
- > IsoFlange™ Technology
- > SymmHeat™ Technology

Single Wafer Performance with Cluster Tool Productivity Benefits



Seamless process transfer to large wafer



Find out more at www.veeco/propel
or call 1.888.24.VEECO

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